Correction to Room-Temperature Ferroelectric Resistive Switching in Ultrathin $Pb(Zr_{0.2}Ti_{0.8})O_3$ Films

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Daniel Pantel,* Silvana Goetze, Dietrich Hesse, and Marin Alexe

In the lower part of Figure 4, the resistance *R* should be given in units of GΩ instead of MΩ. This does not influence any conclusions drawn from the article.

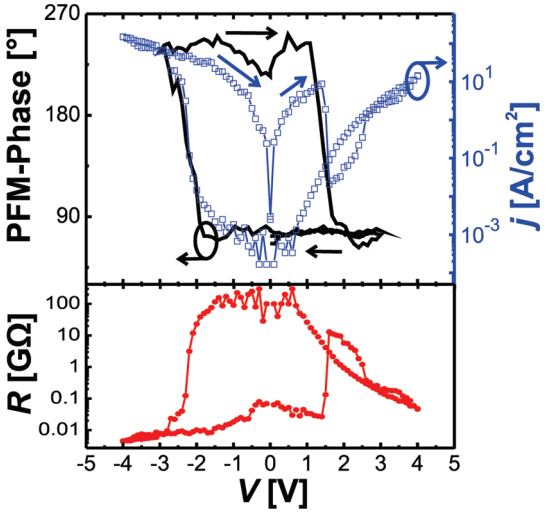

Figure 4. *IV* and remnant PFM-phase hysteresis on the same device (thickness: 9 nm, area: 0.6 μm^2) in consecutive measurements. The coercive voltages of ferroelectric switching and current switching are identical within the limits of the ac PFM probing voltage of 0.5 V. The lower panel provides additionally the voltage, *V*, dependence of the resistance, *R*.

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